

MOSFETs Silicon N-channel MOS (U-MOSIV)

# **TPCC8069**

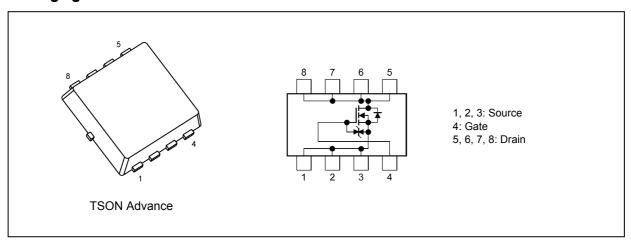
### 1. Applications

- · Motor Drivers
- · DC-DC Converters
- Switching Voltage Regulators

#### 2. Features

- (1) Small, thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 6.5 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (3) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- (4) Enhancement mode:  $V_{th} = 2.0 \text{ to } 3.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1.0 \text{ mA)}$

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25°C unless otherwise specified)

Characteris	stics		Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	40	V
Gate-source voltage			V <sub>GSS</sub>	±20	
Drain current (DC)		(Note 1)	I <sub>D</sub>	30	Α
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	90	
Power dissipation	$(T_c = 25^{\circ}C)$		$P_{D}$	46.8	W
Power dissipation	(t = 10 s)	(Note 2)	$P_{D}$	2.27	W
Power dissipation	(t = 10 s)	(Note 3)	$P_{D}$	0.84	8
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	78.9	mJ
Avalanche current			I <sub>AR</sub>	30	Α
Channel temperature	- -	(Note 5)	T <sub>ch</sub>	175	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



#### 5. Thermal Characteristics

Characteristics			Symbol	Max	Unit
Channel-to-case thermal resistance	(T <sub>c</sub> = 25°C)		R <sub>th(ch-c)</sub>	3.2	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 2)	R <sub>th(ch-a)</sub>	66	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R <sub>th(ch-a)</sub>	178	°C/W

Note 1: Ensure that the channel temperature does not exceed 175°C.

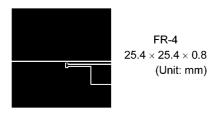
Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

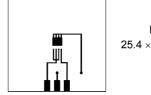
Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4:  $V_{DD}$  = 25 V,  $T_{ch}$  = 25°C (initial), L = 91  $\mu$ H,  $R_{G}$  = 25  $\Omega$ ,  $I_{AR}$  = 30 A

Note 5: Merely channel temperature is guaranteed 175°C.

Storage temperature range is guaranteed as usual (-55 to 150°C).





FR-4  $25.4 \times 25.4 \times 0.8$  (Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	40	_	_	٧
	V <sub>(BR)DSX</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	20	_		
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.0 mA	2.0	_	3.0	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 6 V, I <sub>D</sub> = 15 A	_	8.8	14.1	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A		6.5	8.1	

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	1640	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	200	_	
Output capacitance	C <sub>oss</sub>		_	340	_	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	7	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	16	_	
Switching time (fall time)	t <sub>f</sub>		_	14	_	
Switching time (turn-off time)	t <sub>off</sub>		_	41		

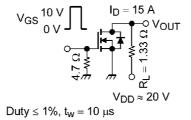


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	_	34	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	8	_	
Gate-drain charge	$Q_{gd}$		_	12	_	

# 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 6)	I <sub>DRP</sub>	_	_	_	90	Α
Diode forward voltage		$V_{DSF}$	I <sub>DR</sub> = 30 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V

Note 6: Ensure that the channel temperature does not exceed 175°C.



# 7. Marking

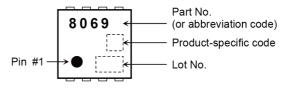


Fig. 7.1 Marking

### 8. Characteristics Curves (Note)

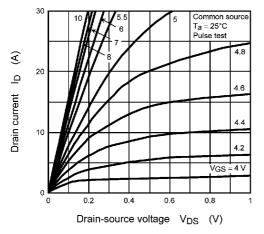
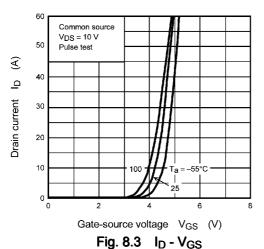


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>



Common source

T<sub>a</sub> = 25°C Pulse test

Drain current  $I_D$  (A) Fig. 8.5 RDS(ON) -  $I_D$ 

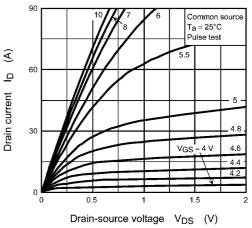


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

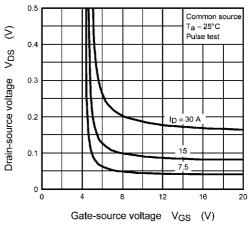


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

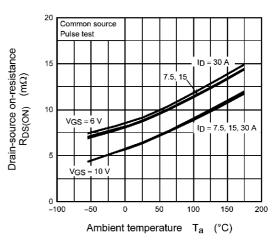


Fig. 8.6 R<sub>DS(ON)</sub> - T<sub>a</sub> (Note 7)

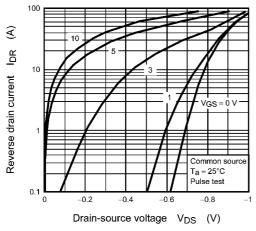


Fig. 8.7  $I_{DR}$  -  $V_{DS}$ 

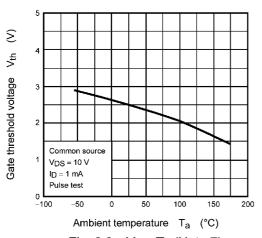


Fig. 8.9 V<sub>th</sub> - T<sub>a</sub> (Note 7)

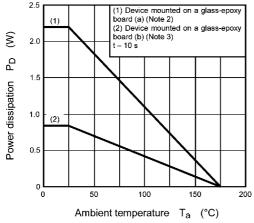


Fig. 8.11 P<sub>D</sub> - T<sub>a</sub> (Note 7) (Guaranteed Maximum)

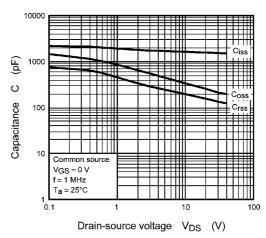


Fig. 8.8 Capacitance - V<sub>DS</sub>

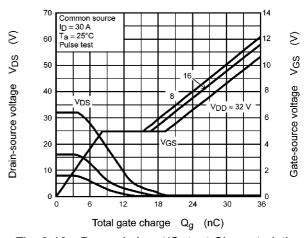


Fig. 8.10 Dynamic Input/Output Characteristics

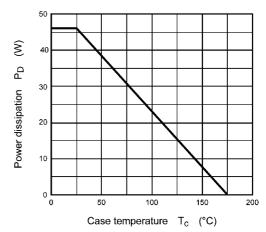


Fig. 8.12 P<sub>D</sub> - T<sub>c</sub> (Note 7) (Guaranteed Maximum)

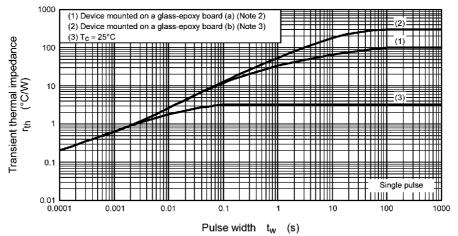


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)

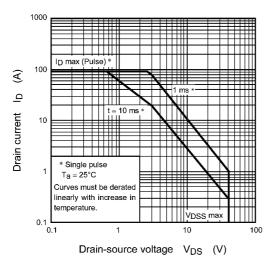


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

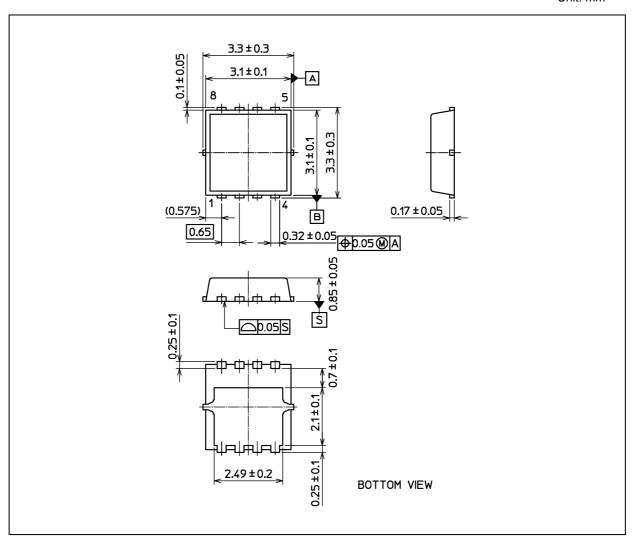
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Note 7: Although several performance curves are shown up to a  $T_a$  or  $T_c$  of 175°C, the device is not guaranteed at storage temperatures up to 175°C. The storage temperature ( $T_{stg}$ ) range is rated at -55°C to 150°C.



### **Package Dimensions**

Unit: mm



Weight: 0.02 g (typ.)

Pa	ackage Name(s)
TOSHIBA: 2-3X1S	
Nickname: TSON Advance	



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